



# SGM8261-5

## Bipolar-Input, High Performance, Ultra-Low Noise HiFi Audio Headset Driver

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### GENERAL DESCRIPTION

The SGM8261-5 is a dual, bipolar-input, low noise operational amplifier optimized for high voltage systems. The device operates from 3.6V to 36V single supply or from  $\pm 3.6V$  to  $\pm 18V$  dual power supplies, while consuming 4.1mA quiescent current per amplifier.

The SGM8261-5 has impressive dynamic characteristics with various loads. The rail-to-rail output voltage range is from  $(-V_S) + 0.15V$  to  $(+V_S) - 0.15V$  when  $2k\Omega$  load resistor is tied from OUT pin to  $V_S/2$ . This results in large headroom and wide dynamic range. The SGM8261-5 is unity-gain stable and offers a  $\pm 110mA$  high output current. It features  $1.6nV/\sqrt{Hz}$  ultra-low noise at 1kHz with 0.00002% distortion.

The SGM8261-5 is available in Green MSOP-10 and TDFN-3x3-10L packages. It operates over an ambient temperature range of  $-40^\circ C$  to  $+85^\circ C$ .

### FEATURES

- Excellent Sound Quality
- Ultra-Low Input Voltage Noise:  $1.6nV/\sqrt{Hz}$  at 1kHz
- Ultra-Low Distortion: 0.00002% at 1kHz
- Low Offset Voltage:  $\pm 350\mu V$  (MAX)
- Unity-Gain Stable
- Gain-Bandwidth Product: 16MHz (G = +1)
- High Slew Rate: 16V/ $\mu s$
- High Open-Loop Gain: 150dB
- Rail-to-Rail Output
- Support Single or Dual Power Supplies:  
3.6V to 36V or  $\pm 3.6V$  to  $\pm 18V$
- Low Quiescent Current: 4.1mA/Amplifier
- $-40^\circ C$  to  $+85^\circ C$  Operating Temperature Range
- Available in Green MSOP-10 and TDFN-3x3-10L Packages

### APPLICATIONS

Professional Audio Instrument  
High-End A/V Receiving Machines  
Analog and Digital Mixing Control Boards

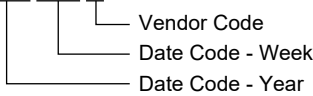
**PACKAGE/ORDERING INFORMATION**

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM8261-5	MSOP-10	-40°C to +85°C	SGM8261-5YMS10G/TR	SGM82615 YMS10 XXXXX	Tape and Reel, 4000
	TDFN-3x3-10L	-40°C to +85°C	SGM8261-5YTD10G/TR	SGM 82615D XXXXX	Tape and Reel, 4000

**MARKING INFORMATION**

NOTE: XXXXX = Date Code and Vendor Code.

**XXXXX**



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

**ABSOLUTE MAXIMUM RATINGS**

- Supply Voltage, +V<sub>s</sub> to -V<sub>s</sub>..... 40V
- Input Voltage Range .....(-V<sub>s</sub>) - 0.3V to (+V<sub>s</sub>) + 0.3V
- EN to GND.....-0.3V to 5.5V
- Input Current (All pins except power supply pins)..... ±10mA
- Output Short-Circuit Current ..... ±180mA
- Junction Temperature.....+150°C
- Storage Temperature Range .....-65°C to +150°C
- Lead Temperature (Soldering, 10s).....+260°C
- ESD Susceptibility
- HBM..... 8000V
- MM..... 300V
- CDM ..... 1000V

**RECOMMENDED OPERATING CONDITIONS**

- Operating Temperature Range .....-40°C to +85°C

**OVERSTRESS CAUTION**

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to

absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

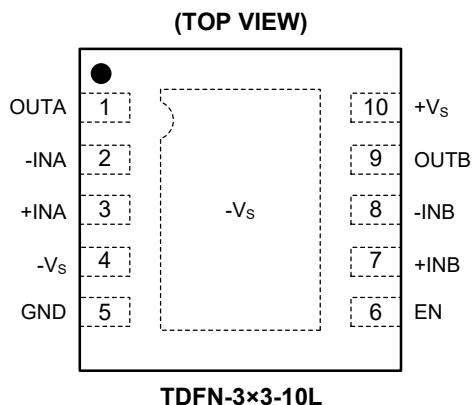
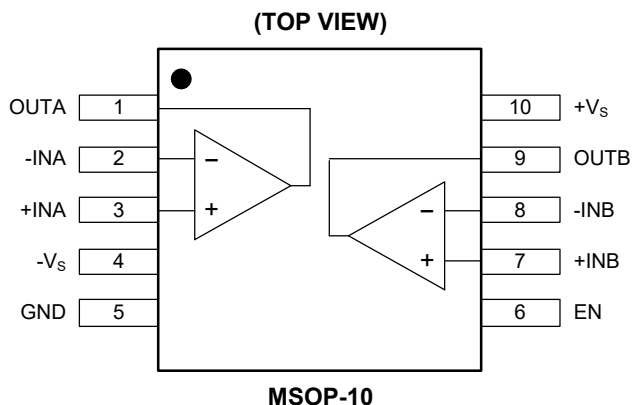
**ESD SENSITIVITY CAUTION**

This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

**DISCLAIMER**

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

**PIN CONFIGURATIONS**



NOTE: For TDFN-3x3-10L package, connect thermal die pad to -Vs. Connect it to -Vs plane to maximize thermal performance.

**ELECTRICAL CHARACTERISTICS**(At  $T_A = +25^\circ\text{C}$ ,  $V_S = \pm 5\text{V}$  to  $\pm 18\text{V}$ ,  $\text{GND} = 0\text{V}$ ,  $R_L = 2\text{k}\Omega$ ,  $V_{\text{CM}} = V_{\text{OUT}} = V_S/2$ , unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
<b>Input Characteristics</b>					
Input Offset Voltage ( $V_{\text{OS}}$ )	$V_S = \pm 15\text{V}$		$\pm 100$	$\pm 350$	$\mu\text{V}$
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			$\pm 450$	
Input Offset Voltage Drift ( $\Delta V_{\text{OS}}/\Delta T$ )	$V_S = \pm 15\text{V}$		1		$\mu\text{V}/^\circ\text{C}$
Input Bias Current ( $I_B$ )	$V_{\text{CM}} = V_{\text{OUT}} = V_S/2$		$\pm 40$	$\pm 300$	nA
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			$\pm 550$	
Input Offset Current ( $I_{\text{OS}}$ )	$V_{\text{CM}} = V_{\text{OUT}} = V_S/2$		$\pm 25$	$\pm 165$	nA
Input Common Mode Voltage Range ( $V_{\text{CM}}$ )		$(-V_S) + 1.8$		$(+V_S) - 1.8$	V
Common Mode Rejection Ratio (CMRR)	$V_S = \pm 5\text{V}$ , $(-V_S) + 1.8\text{V} \leq V_{\text{CM}} \leq (+V_S) - 1.8\text{V}$	114	130		dB
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	111			
	$V_S = \pm 18\text{V}$ , $(-V_S) + 1.8\text{V} \leq V_{\text{CM}} \leq (+V_S) - 1.8\text{V}$	125	136		dB
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	120			
Open-Loop Voltage Gain ( $A_{\text{OL}}$ )	$V_S = \pm 5\text{V}$ to $\pm 18\text{V}$ , $(-V_S) + 0.2\text{V} \leq V_{\text{OUT}} \leq (+V_S) - 0.2\text{V}$ , $R_L = 10\text{k}\Omega$	122	150		dB
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	119			
	$V_S = \pm 5\text{V}$ to $\pm 18\text{V}$ , $(-V_S) + 0.6\text{V} \leq V_{\text{OUT}} \leq (+V_S) - 0.6\text{V}$ , $R_L = 2\text{k}\Omega$	123	150		
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$	120			
<b>Input Impedance</b>					
Differential			$32\text{k} \parallel 10$		$\Omega \parallel \text{pF}$
Common Mode			$10^9 \parallel 4$		$\Omega \parallel \text{pF}$
<b>Output Characteristics</b>					
Output Voltage Swing from Rail	$V_S = \pm 5\text{V}$ to $\pm 18\text{V}$ , $R_L = 10\text{k}\Omega$		$\pm 35$	$\pm 50$	mV
	$V_S = \pm 5\text{V}$ to $\pm 18\text{V}$ , $R_L = 2\text{k}\Omega$		$\pm 150$	$\pm 210$	
Output Short-Circuit Current ( $I_{\text{SC}}$ )	$V_S = \pm 3.6\text{V}$ to $\pm 18\text{V}$		$\pm 110$		mA
<b>Audio Performance</b>					
Total Harmonic Distortion + Noise (THD+N)	$G = +1$ , $V_{\text{OUT}} = 3V_{\text{RMS}}$ , $f = 1\text{kHz}$		0.00002		%
			-134		dB
Intermodulation Distortion (IMD)	$G = +1$ , $V_{\text{OUT}} = 3V_{\text{RMS}}$ , SMPTE/DIN, Two-Tone, 4:1 (60Hz and 7kHz)		0.000015		%
			-136		dB
	$G = +1$ , $V_{\text{OUT}} = 3V_{\text{RMS}}$ , DIM 30, (3kHz square wave and 15kHz sine wave)		0.000032		%
			-130		dB
$G = +1$ , $V_{\text{OUT}} = 3V_{\text{RMS}}$ , CCIF Twin-Tone, (19kHz and 20kHz)		0.00013		%	
		-118		dB	
<b>Frequency Response</b>					
Gain-Bandwidth Product (GBP)	$G = +100$		45		MHz
	$G = +1$		16		
Slew Rate (SR)	$G = -1$		16		V/ $\mu\text{s}$
Full Power Bandwidth <sup>(1)</sup>	$V_{\text{OUT}} = 1V_{\text{P-P}}$		2		MHz
Overload Recovery Time	$G = -10$		500		ns
Channel Separation (Dual)	$f = 1\text{kHz}$		-140		dB

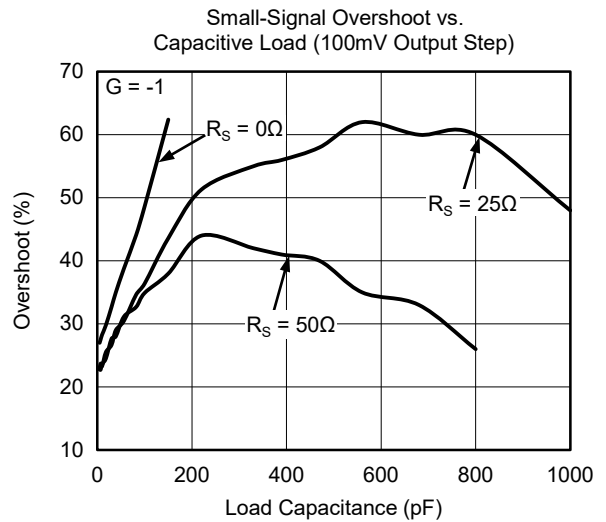
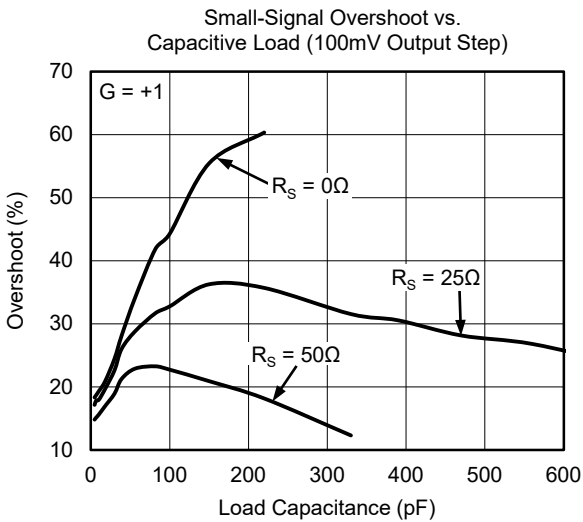
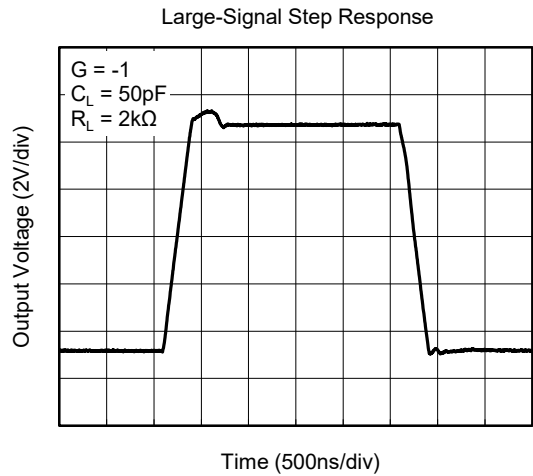
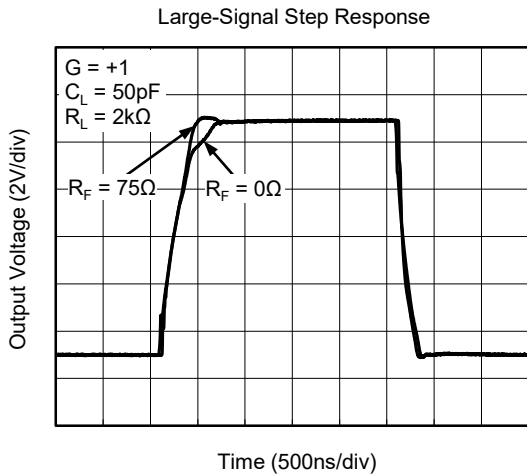
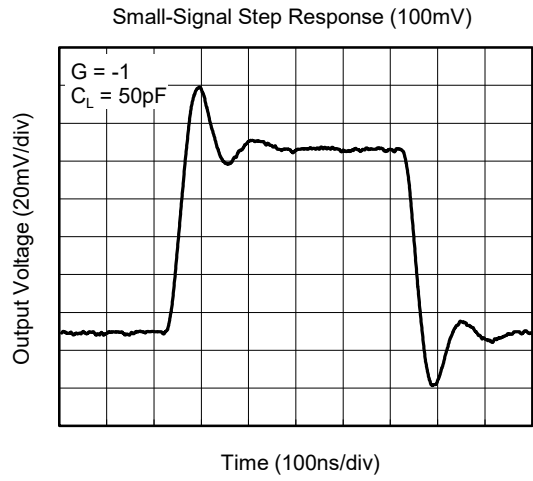
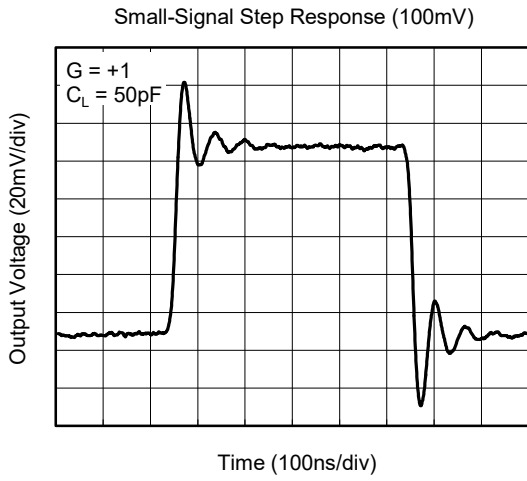
NOTE: 1. Full-power bandwidth equals to the value of slew rate/( $2\pi \times V_P$ ).

**ELECTRICAL CHARACTERISTICS (continued)**(At  $T_A = +25^\circ\text{C}$ ,  $V_S = \pm 5\text{V}$  to  $\pm 18\text{V}$ ,  $\text{GND} = 0\text{V}$ ,  $R_L = 2\text{k}\Omega$ ,  $V_{\text{CM}} = V_{\text{OUT}} = V_S/2$ , unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
<b>Noise Performance</b>					
Input Voltage Noise	$f = 20\text{Hz}$ to $20\text{kHz}$		1.7		$\mu\text{V}_{\text{P-P}}$
Input Voltage Noise Density ( $e_n$ )	$f = 10\text{Hz}$		5		$\text{nV}/\sqrt{\text{Hz}}$
	$f = 100\text{Hz}$		2		
	$f = 1\text{kHz}$		1.6		
Input Current Noise Density ( $i_n$ )	$f = 1\text{kHz}$		6		$\text{pA}/\sqrt{\text{Hz}}$
<b>Power Supply</b>					
Supply Voltage ( $V_S$ )		$\pm 3.6$		$\pm 18$	V
Specified Voltage ( $V_S$ )		$\pm 5$		$\pm 18$	V
Quiescent Current/Amplifier ( $I_Q$ )	$I_{\text{OUT}} = 0$		4.1	5.5	mA
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			5.8	
Shutdown Current ( $I_{\text{SHDN}}$ )	$V_S = \pm 5\text{V}$ to $\pm 18\text{V}$ , $I_{\text{OUT}} = 0\text{A}$ , $\text{EN} = \text{GND}$		100	200	$\mu\text{A}$
Power Supply Rejection Ratio (PSRR)	$V_S = \pm 3.6\text{V}$ to $\pm 18\text{V}$		0.1	0.6	$\mu\text{V}/\text{V}$
	$-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$			1.6	
<b>EN Control</b>					
Input High Voltage ( $V_{\text{IH}}$ )	$V_S = \pm 3.6\text{V}$ to $\pm 18\text{V}$ , $\text{GND} = 0\text{V}$	1.8		MIN ( $5, +V_S$ )	V
Input Low Voltage ( $V_{\text{IL}}$ )	$V_S = \pm 3.6\text{V}$ to $\pm 18\text{V}$ , $\text{GND} = 0\text{V}$			0.4	V
Input Leakage Current ( $I_{\text{IN}}$ )	$V_S = \pm 5\text{V}$ to $\pm 18\text{V}$ , $\text{GND} = 0\text{V}$ , $\text{EN} = 0\text{V}$ or $5\text{V}$		1	1.8	$\mu\text{A}$
EN Pull-Down Resistor ( $R_{\text{EN}}$ )			4		$\text{M}\Omega$

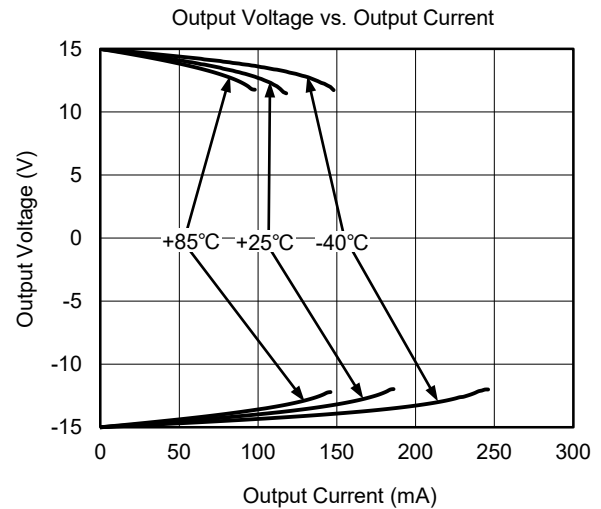
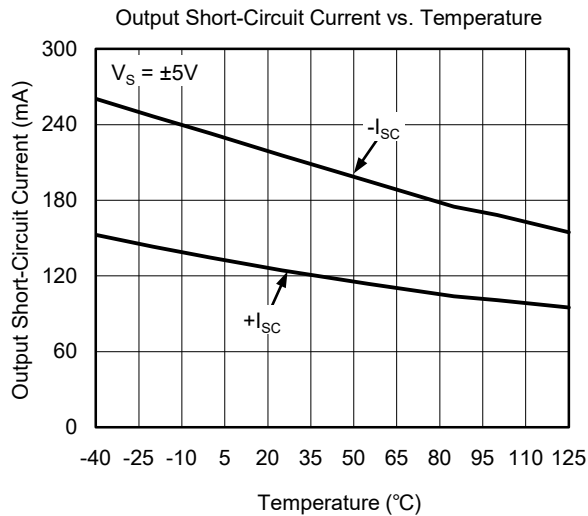
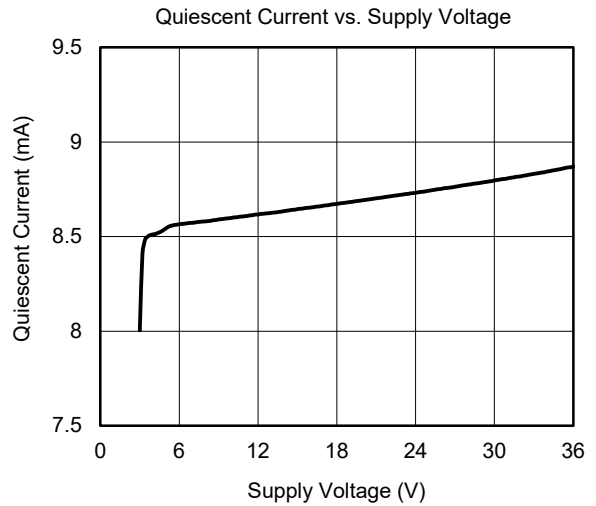
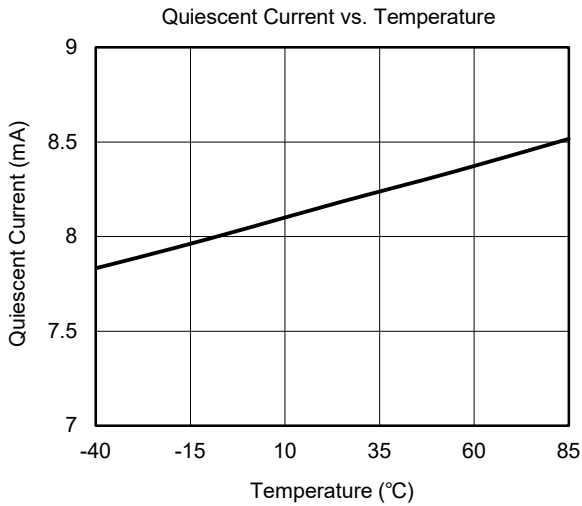
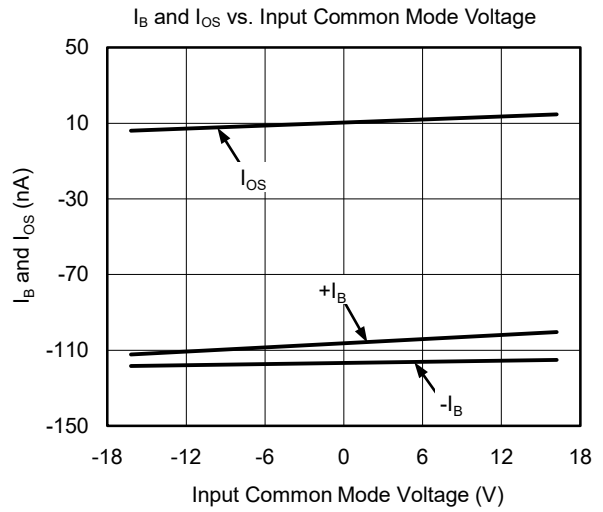
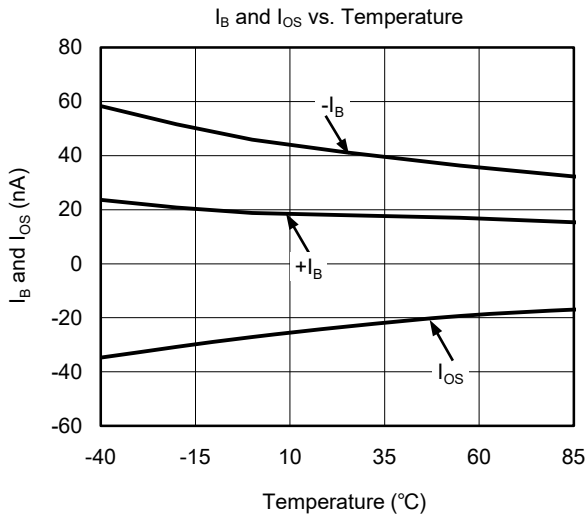
**TYPICAL PERFORMANCE CHARACTERISTICS**

At  $T_A = +25^\circ\text{C}$ ,  $V_S = \pm 15\text{V}$ ,  $\text{GND} = 0\text{V}$  and  $R_L = 2\text{k}\Omega$ , unless otherwise noted.



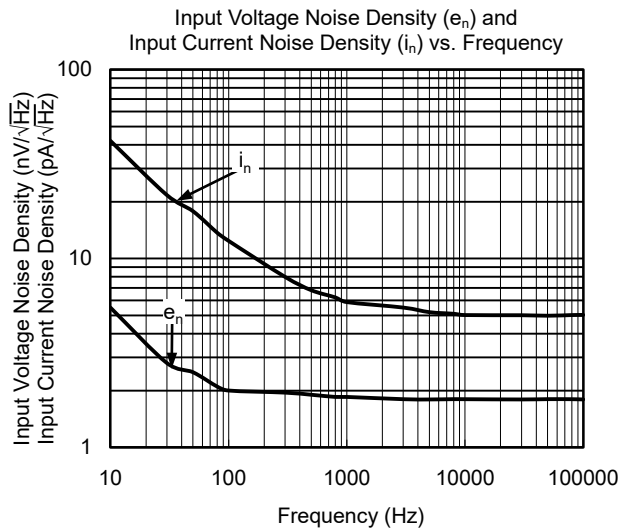
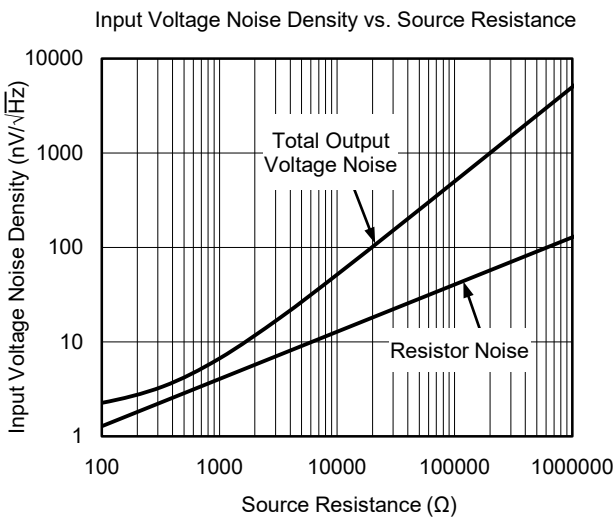
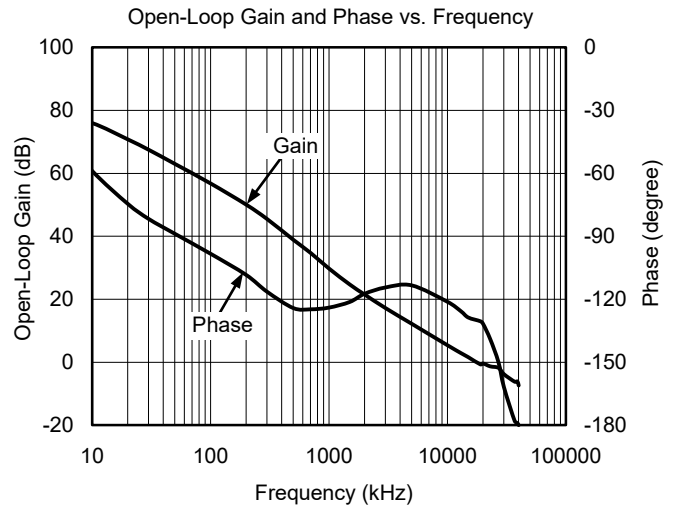
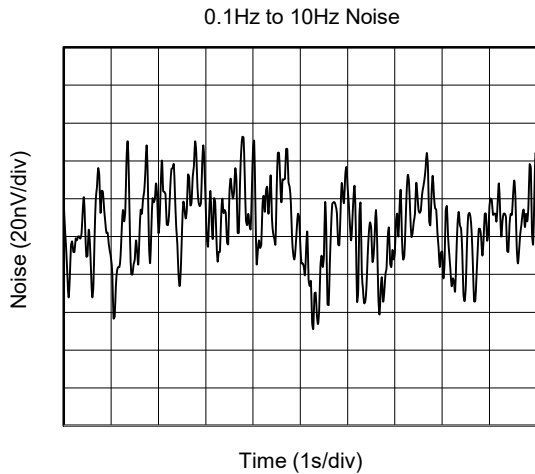
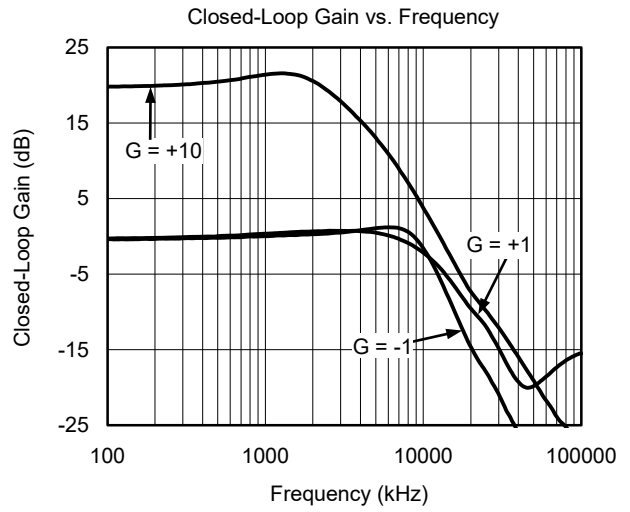
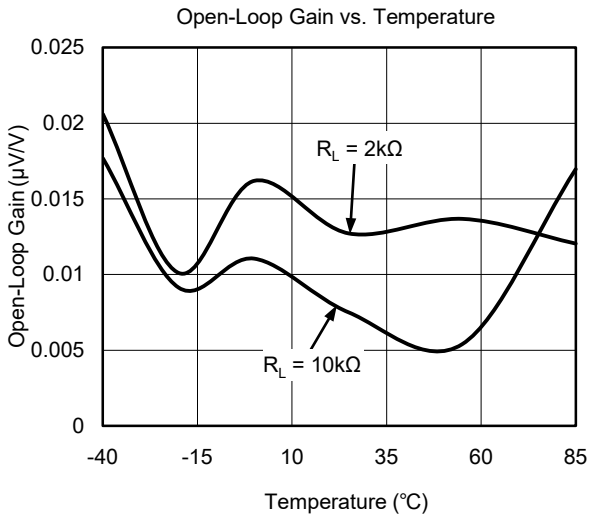
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**TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

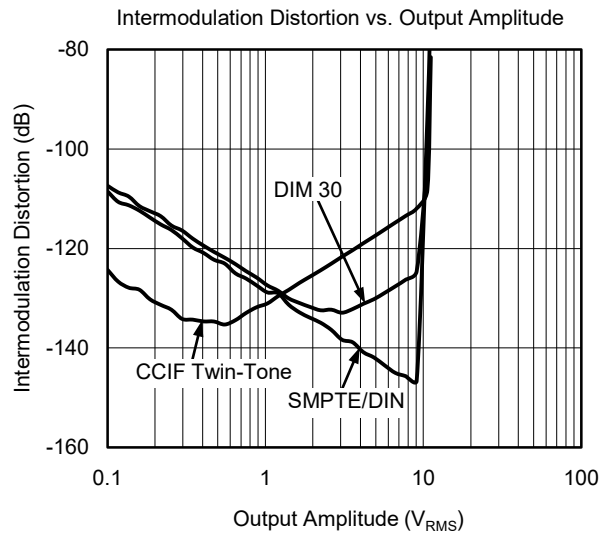
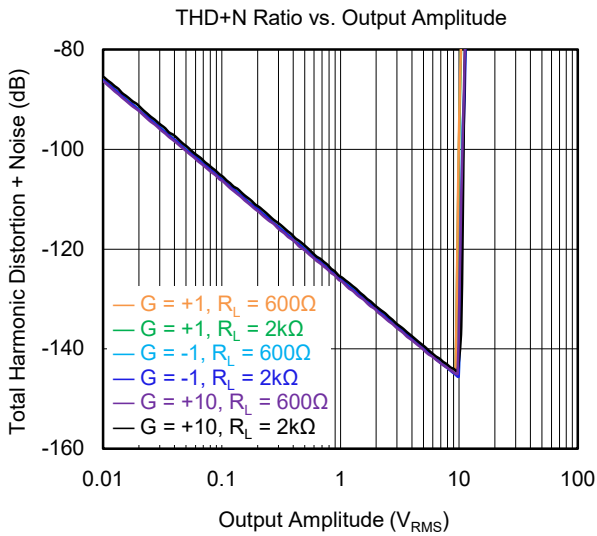
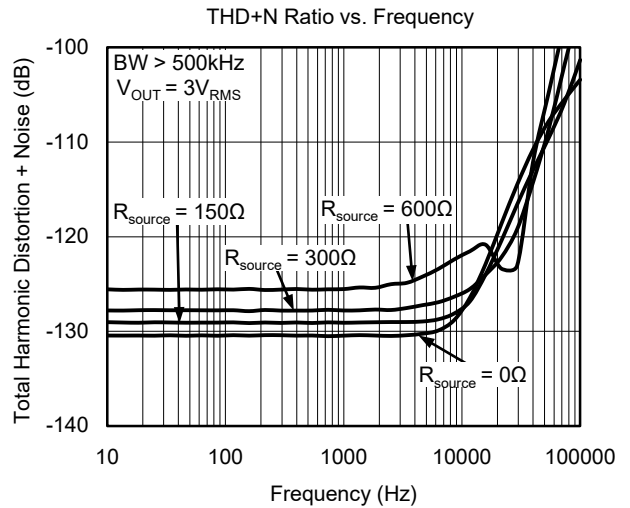
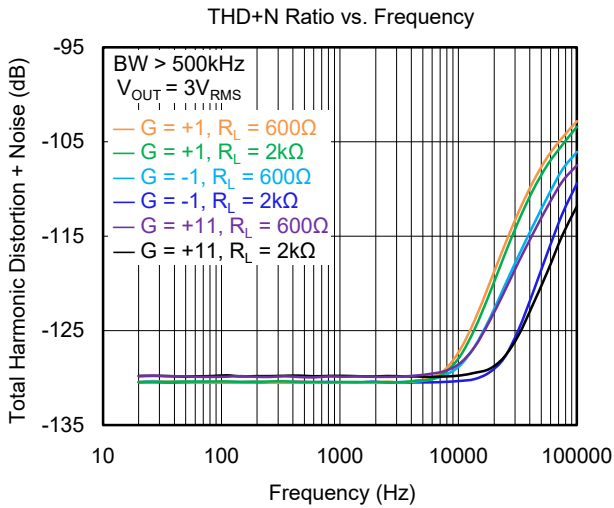
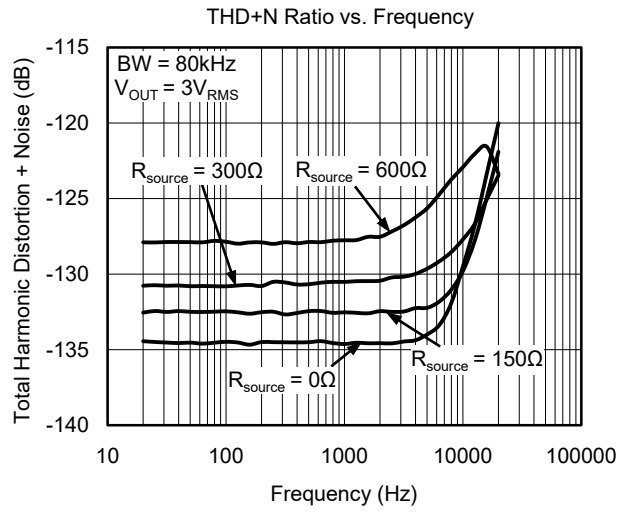
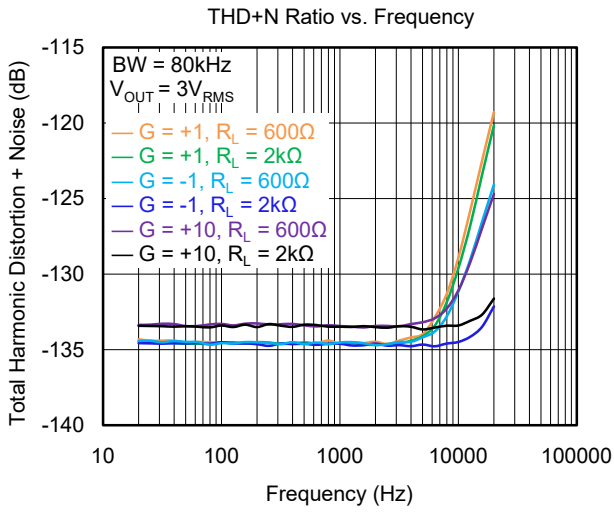
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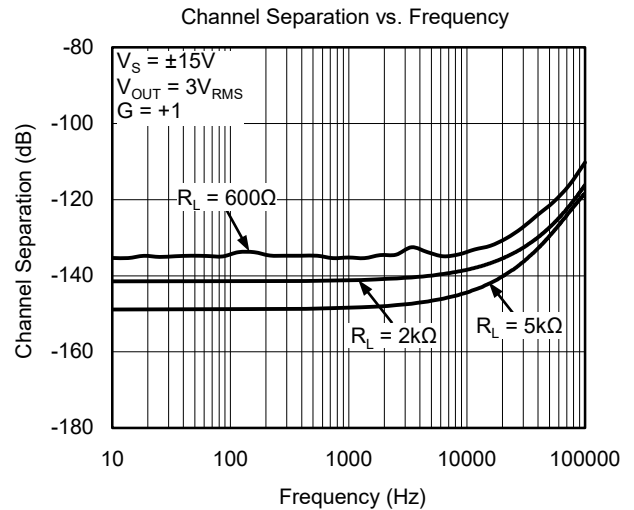
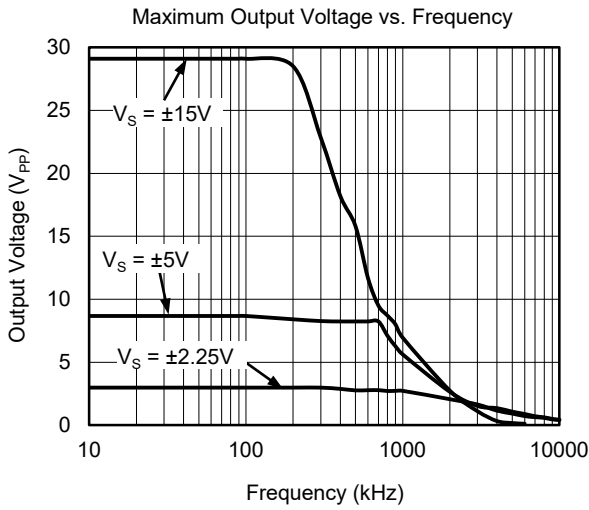
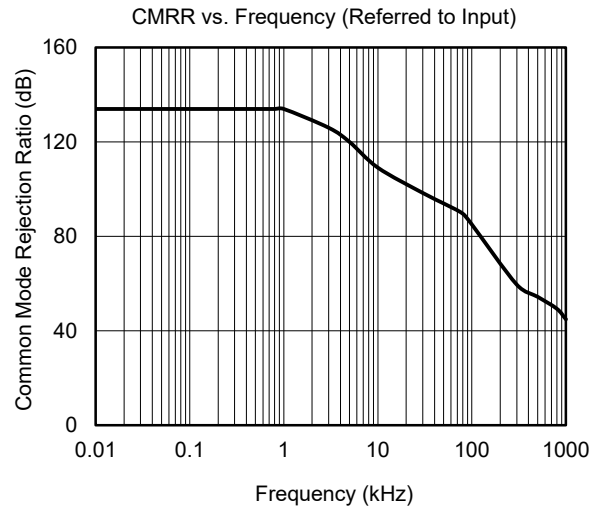
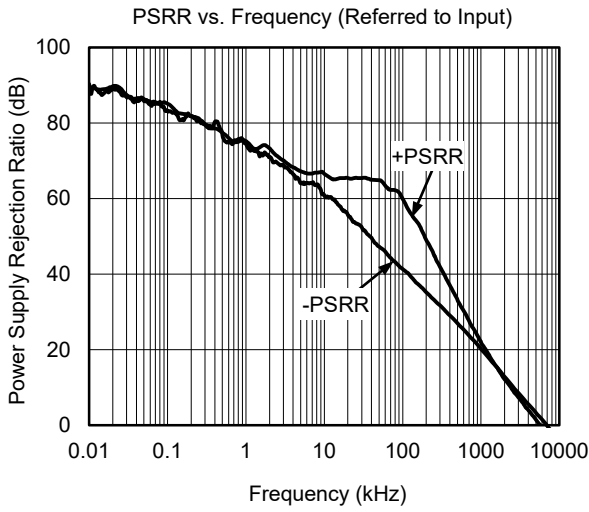
**TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

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**TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

At  $T_A = +25^\circ\text{C}$ ,  $V_S = \pm 15\text{V}$ ,  $\text{GND} = 0\text{V}$  and  $R_L = 2\text{k}\Omega$ , unless otherwise noted.



**APPLICATION INFORMATION**

The benefit of SGM8261-5 is that it can maintain stability at unity-gain and the noise of it is extreme low; and there is no output phase reversal for this driver. For noisy power supplies, a decoupling capacitor is necessary for operation. It is recommended that a 0.1µF capacitor can be taken into account.

For normal operation, the single power supply range is from 3.6V to 36V while dual power supply range is from ±3.6V to ±18V. However, in some special cases, the absolute values of positive and negative power supplies are not equal to dual power supply operations, and SGM8261-5 can work well in this case. For instance, the positive value of power supply is 25V while the negative one is -5V. For normal operation, the users should always make sure that the common mode voltage at the input of the driver is within the typical range. Also, the typical temperature range to ensure that the driver can work in normal is from -40°C to +85°C.

**Input Protection**

The back-to-back diode is used to protect the input from large differential input voltage. However, there is no consequence for it in wide range of the applications. Also, for the application of  $G = +1$ , the diode can forward bias the input signal with fast ramp as the operational amplifier cannot respond quickly for it. The input current should be limited within the range of 10mA for the forward bias of the internal back-to-back diode, and the user can use  $R_F$  and  $R_I$  externally to limit the input current. Unfortunately, the external resistors can degrade the low noise performance of SGM8261-5, and the following figure illustrates the application with the resistors of  $R_F$  and  $R_I$ .

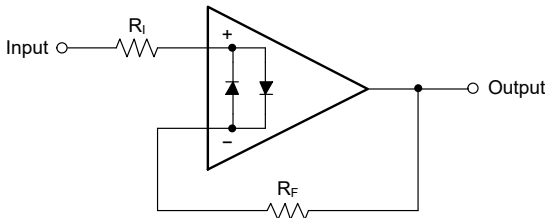


Figure 1. Input Current Limit

**Noise Performance**

The equation of the circuit noise for the application of unity-gain for varying source impedance is shown in Equation 1. However, there is no addition noise condition for  $R_F$  in the application of Figure 2.

For the application in Figure 2, the gain-bandwidth product is 16MHz in the unity-gain condition. For the noise contribution of the operational amplifier, there are components of current and voltage noise. The  $V_{OS}$  is modeled as the time-varying voltage component of the noise contribution. The  $I_B$  is modeled as the time-varying current component of the noise contribution, and this  $I_B$  is multiplied with the source impedance  $R_S$  to obtain a voltage component. Therefore, the value of  $R_S$  depends on the level of circuit noise (Figure 2). If the value of  $R_S$  is low, the voltage noise  $e_n^2$  will dominate to the contribution of the noise. Because of the benefit of the noise performance, SGM8261-5 will be a good choice for the application where the source impedance  $R_S$  is below 1kΩ.

The calculation of the circuit noise for Figure 2 is shown as below:

$$E_o^2 = e_n^2 + (i_n R_S)^2 + 4kTR_S \tag{1}$$

where:

$e_n$  is the voltage noise.

$i_n$  is the current noise.

$R_S$  is the source impedance.

$k$  is the Boltzmann's constant, which is  $1.38 \times 10^{-23}$  J/K.

$T$  is the temperature in Kelvin (K).

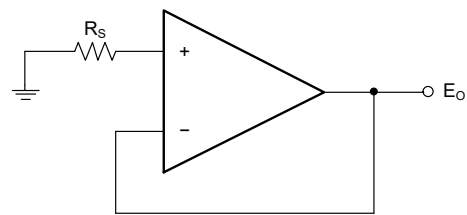


Figure 2. Unity-Gain Buffer Configuration

APPLICATION INFORMATION (continued)

Calculations of Basic Noise Condition

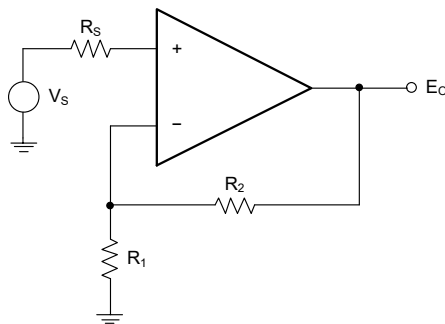
For the application of low noise condition, there are several noise sources should be taken into account, which are the noise generated from the signal source, feedback resistor and the operational amplifier itself. To convert them to the format of noise and calculate the total generated noise from the circuit, these components should be summed using root-square.

The thermal noise of the circuit is produced by the resistances of the circuit. To reduce the total noise contribution of the circuit, it is recommended that selecting

small value of resistors and using SGM8261-5 will be a good choice.

The topology of non-inverting and inverting amplifiers with gain is shown in Figure 3. In these configurations, the noise is contributed by the feedback resistor  $R_2$ .

The voltage noise components can be created by the current noise reacts with the feedback resistor. To minimize these sources of noise, the selection of the feedback resistor  $R_2$  is significant. The following equations illustrate the details of the noise configuration.



Noise in Non-Inverting Gain Configuration

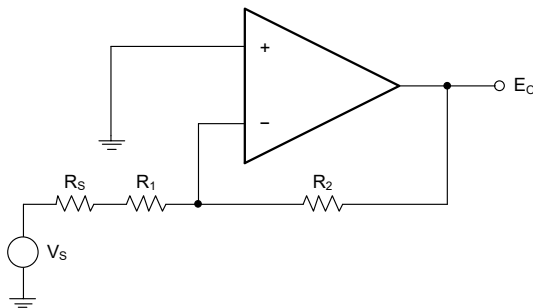
Noise at the output:

$$E_o^2 = \left[ 1 + \frac{R_2}{R_1} \right]^2 e_n^2 + e_1^2 + e_2^2 + (i_n R_2)^2 + e_s^2 + (i_n R_s)^2 \left[ 1 + \frac{R_2}{R_1} \right]^2$$

where  $e_s = \sqrt{4kTR_s} \times \left[ 1 + \frac{R_2}{R_1} \right]$  = thermal noise of  $R_s$

$$e_1 = \sqrt{4kTR_1} \times \left[ \frac{R_2}{R_1} \right]$$
 = thermal noise of  $R_1$

$$e_2 = \sqrt{4kTR_2}$$
 = thermal noise of  $R_2$



Noise in Inverting Gain Configuration

Noise at the output:

$$E_o^2 = \left[ 1 + \frac{R_2}{R_1 + R_s} \right]^2 e_n^2 + e_1^2 + e_2^2 + (i_n R_2)^2 + e_s^2$$

where  $e_s = \sqrt{4kTR_s} \times \left[ \frac{R_2}{R_1 + R_s} \right]$  = thermal noise of  $R_s$

$$e_1 = \sqrt{4kTR_1} \times \left[ \frac{R_2}{R_1 + R_s} \right]$$
 = thermal noise of  $R_1$

$$e_2 = \sqrt{4kTR_2}$$
 = thermal noise of  $R_2$

NOTE: At 1kHz, the noise densities of voltage and current are equal to  $1.6nV/\sqrt{Hz}$  and  $6pA/\sqrt{Hz}$  respectively.

Figure 3. Noise Calculation in Gain Configurations

APPLICATION INFORMATION (continued)

**Total Harmonic Distortion Measurements**

The distortion characteristics of SGM8261-5 is excellent, and the value of THD + N is lower than 0.00015% ( $G = +1$ ,  $V_{OUT} = 3V_{RMS}$ ,  $BW = 80kHz$ ) over the range of 20Hz to 20kHz with a 2kΩ load.

However, the distortion of SGM8261-5 is below the limit of measurement for most of the distortion analyzers. The test circuit in Figure 4 is a good method to measure the distortion accurately by boosting the distortion within the measurement limit.

The distortion of SGM8261-5 can be seen as the internal error of it. For the circuit in Figure 4, the distortion is multiplied by 101 times (40dB). It is equivalent to the noise gain as the resistor  $R_3$  change the noise gain of the non-inverting amplifier while the signal gain remains unchanged so that the measurement resolution is multiplied by 101 times. The condition of load resistor and input signal source is the same as the case without the contribution of  $R_3$ . Also, the value of  $R_3$  should be kept small to reduce the error of distortion measurement.

This technology can boost the distortion so that it is within the capability of the measurement equipment. The noise analyzer and audio precision system two distortion are taken into account to be used to measure the distortion for the value of datasheet, and these types of equipment can simplify the repetitive measurement. However, this distortion can also be measured with the measurement instrument manually.

**Capacitive Loads**

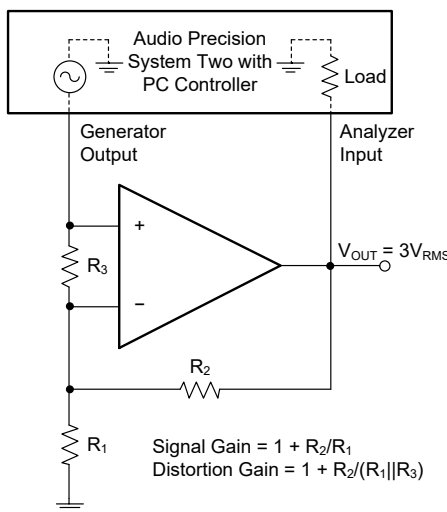
Different gain, load and condition of operation can improve the dynamic characteristics of SGM8261-5. When the closed-loop gain is equal to 1V/V with high capacitive load, the output will be oscillated which means that there is a gain peaking. To improve this issue, it is recommended that isolating the output of the driver and the capacitive load is a good choice. A 50Ω resistor should be taken into account in series with the output.

**Power Dissipation**

A 2kΩ resistive load can be driven with ±18V dual power supplies. The value of power dissipation is proportional to the voltage of power supply. Also, the heat dissipation is improved by the construction of copper leadframe, which is much better than the conventional materials. A good PCB layout can also improve the temperature of junction, which means that the wide trace can dissipate the heat of the driver. Moreover, soldering the driver is better than using a socket for the effect of heat dissipation.

**Electrical Overstress**

The electrical overstress is one of the problems that the users care about. Usually, the issue of the electrical overstress is appeared at the input of the amplifier, but this may involve the voltage level of supply and output pins as well. For the electrical overstress of them, it is determined by the breakdown voltage of the semiconductor and the external circuit which is connected to the specific pin. Moreover, the Electrostatic discharge (ESD) diode is used to prevent the operational amplifier from ESD or high voltage.



Signal Gain =  $1 + R_2/R_1$   
Distortion Gain =  $1 + R_2/(R_1 || R_3)$

Signal Gain	Distortion Gain	R <sub>1</sub>	R <sub>2</sub>	R <sub>3</sub>
+1	101	∞	1kΩ	10Ω
-1	101	4.99kΩ	4.99kΩ	49.9Ω
+10	110	549Ω	4.99kΩ	49.9Ω

Figure 4. Distortion Test Circuit

APPLICATION CIRCUIT

The following figure illustrates the operation of SGM8261-5 in professional audio headphones. The schematic of left stereo channel is shown in Figure 5,

which is equivalent to that of the right stereo channel. An I/V converter and differential multiple feedback (MFB) low-pass filter is used for the quality of the audio signal.

Operating Voltage

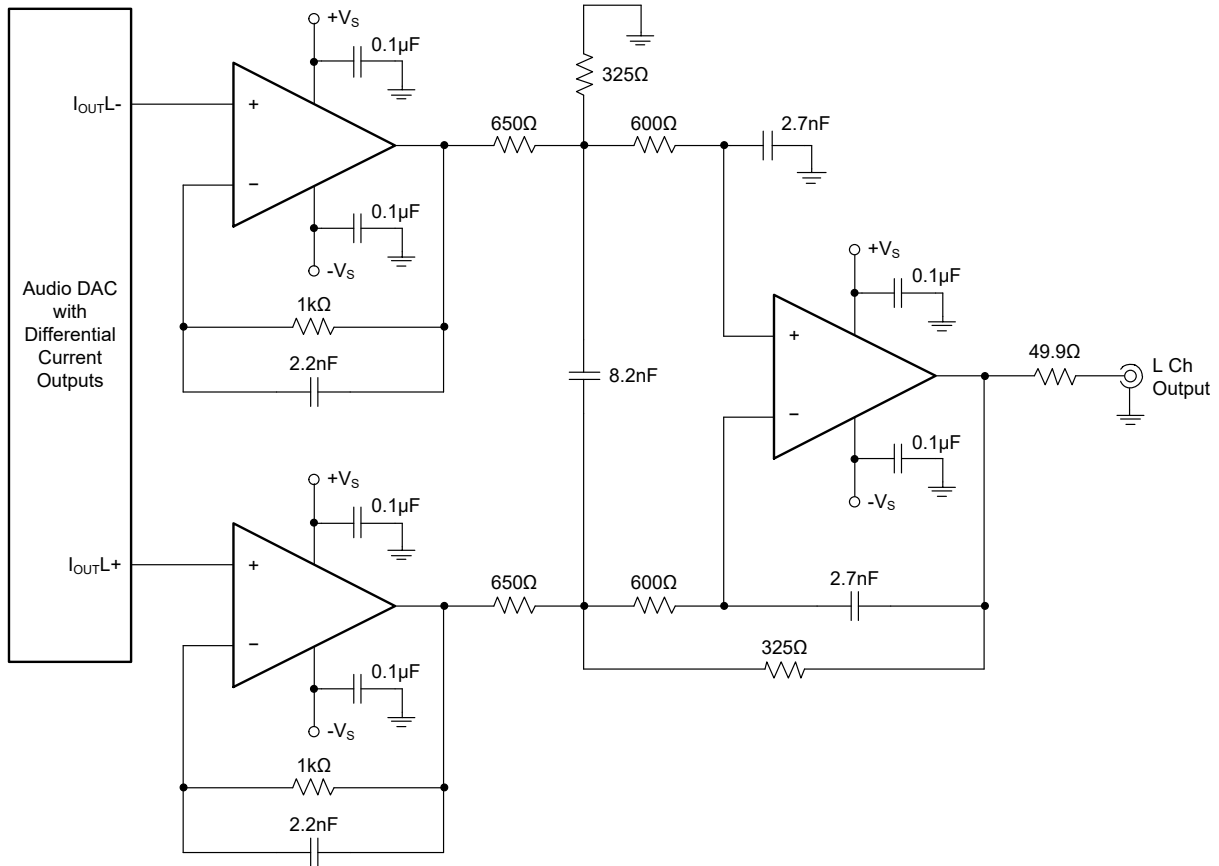


Figure 5. Audio DAC Post Filter (I/V Converter and MFB Differential Low-Pass Filter)

**REVISION HISTORY**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>MAY 2017 – REV.A to REV.A.1</b>	<b>Page</b>
Changed General Description section.....	1

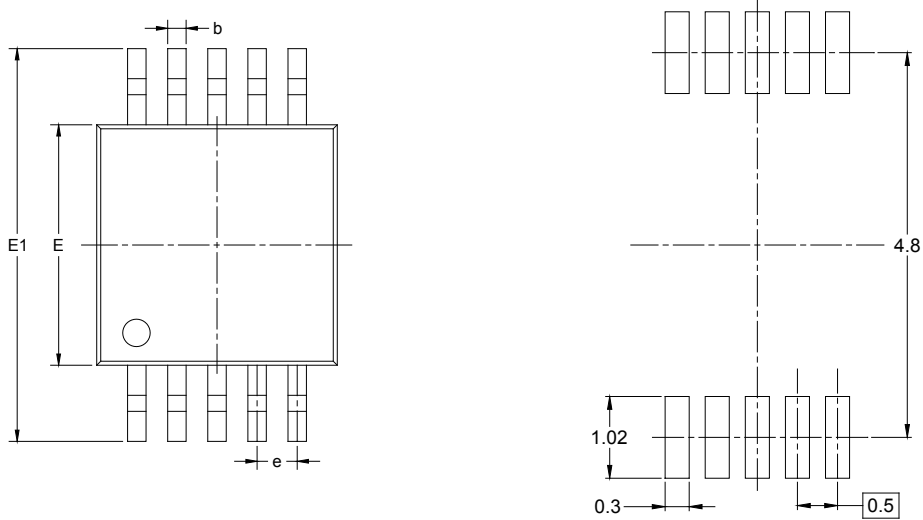
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<b>Changes from Original (MAY 2017) to REV.A</b>	<b>Page</b>
Changed from product preview to production data.....	All

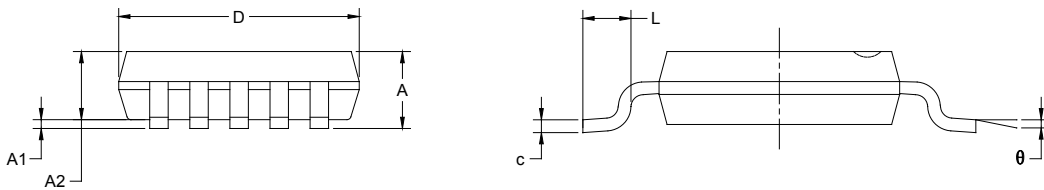
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PACKAGE OUTLINE DIMENSIONS

MSOP-10



RECOMMENDED LAND PATTERN (Unit: mm)

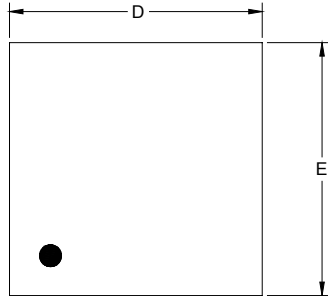


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.820	1.100	0.032	0.043
A1	0.020	0.150	0.001	0.006
A2	0.750	0.950	0.030	0.037
b	0.180	0.280	0.007	0.011
c	0.090	0.230	0.004	0.009
D	2.900	3.100	0.114	0.122
E	2.900	3.100	0.114	0.122
E1	4.750	5.050	0.187	0.199
e	0.500 BSC		0.020 BSC	
L	0.400	0.800	0.016	0.031
θ	0°	6°	0°	6°

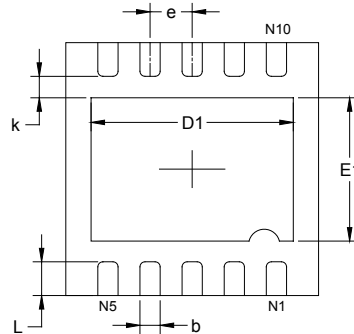


PACKAGE OUTLINE DIMENSIONS

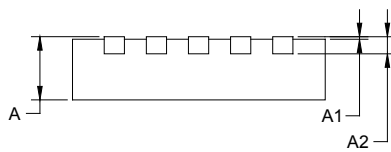
TDFN-3x3-10L



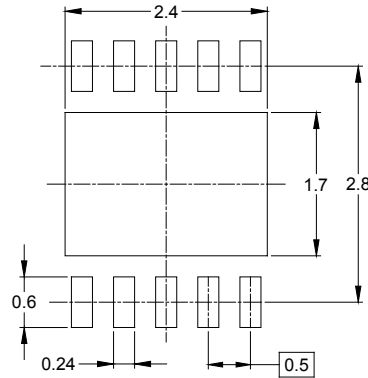
TOP VIEW



BOTTOM VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN (Unit: mm)

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A2	0.203 REF		0.008 REF	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.103
E	2.900	3.100	0.114	0.122
E1	1.500	1.800	0.059	0.071
k	0.200 MIN		0.008 MIN	
b	0.180	0.300	0.007	0.012
e	0.500 TYP		0.020 TYP	
L	0.300	0.500	0.012	0.020

**TAPE AND REEL INFORMATION**

**REEL DIMENSIONS**



**TAPE DIMENSIONS**



NOTE: The picture is only for reference. Please make the object as the standard.

**KEY PARAMETER LIST OF TAPE AND REEL**

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
MSOP-10	13"	12.4	5.20	3.30	1.20	4.0	8.0	2.0	12.0	Q1
TDFN-3×3-10L	13"	12.4	3.35	3.35	1.13	4.0	8.0	2.0	12.0	Q1

DD0001

# PACKAGE INFORMATION

## CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

## KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
13"	386	280	370	5

DD0002